

SN74CBTLV3126 低電圧クワッド FET バス・スイッチ

1 特長

- 標準の 126 タイプのピン配置
- 2 つのポート間を 5Ω スイッチで接続
- データ I/O ポートのレール・ツー・レール・スイッチング
- I_{off} により部分的パワーダウン・モードでの動作をサポート
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能

2 アプリケーション

- データセンターおよびエンタープライズ・コンピューティング
- ブロードバンド固定回線アクセス
- ビル・オートメーション
- 有線ネットワーク
- モーター・ドライブ

3 概要

SN74CBTLV3126 クワッド FET バス・スイッチには、独立のライン・スイッチが搭載されています。各スイッチは、対応する出力イネーブル (OE) 入力がある LOW のときディセーブルになります。

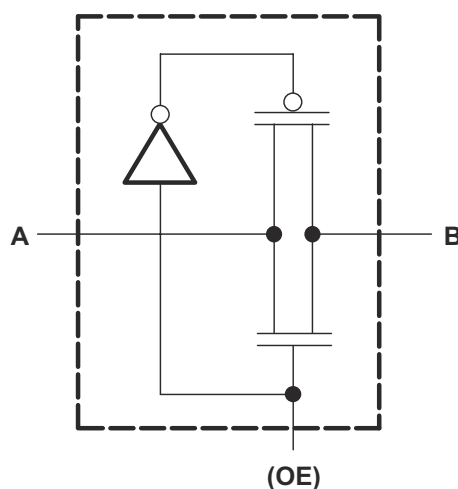
このデバイスは、 I_{off} を使用する部分的パワーダウン・アプリケーション用に完全に動作が規定されています。 I_{off} 機能により、電源オフ時に損傷を引き起こすような電流がデバイスに逆流しないことが保証されます。SN74CBTLV3126 デバイスは、電源オフ時には絶縁されます。

電源オンまたは電源オフ時に高インピーダンス状態を保証するため、OE はプルダウン抵抗経路で GND に接続します。この抵抗の最小値は、ドライバの電流シンク能力によって決定されます。

パッケージ情報⁽¹⁾

部品番号	パッケージ	本体サイズ (公称)
SN74CBTLV3126	SOIC (D) (14)	8.65mm × 3.91mm
	TVSOP (DGV) (14)	3.60mm × 4.40mm
	TSSOP (PW) (14)	5.00mm × 4.40mm
	VQFN (RGY) (14)	4.00mm × 3.50mm
	SSOP (DBQ) (16)	4.90mm × 3.90mm

(1) 利用可能なパッケージについては、データシートの末尾にあるパッケージ・オプションについての付録を参照してください。



概略回路図、各 FET スイッチ



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision K (June 2021) to Revision L (August 2022)	Page
• Updated the <i>Overview</i> section.....	8
Changes from Revision J (January 2019) to Revision K (June 2021)	Page
• 文書全体にわたって表、図、相互参照の採番方法を更新.....	1
• Changed <i>active low</i> to <i>active high</i> in the <i>Pin Configurations and Functions</i> section to reflect logic description change.....	3
Changes from Revision I (October 2003) to Revision J (January 2019)	Page
• 「製品情報」表、「ESD 定格」表、「機能説明」セクション、「デバイスの機能モード」セクション、「アプリケーションと実装」セクション、「電源に関する推奨事項」セクション、「レイアウト」セクション、「デバイスおよびドキュメントのサポート」セクション、「メカニカル、パッケージ、および注文情報」セクションを追加.....	1
• Added V_{IH} MAX values in the <i>Recommended Operating Conditions</i> table.....	5

5 Pin Configuration and Functions

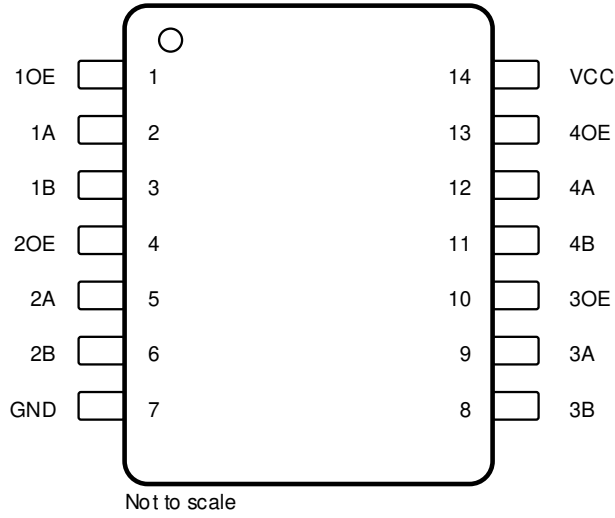


图 5-1. D, DGV, and PW Package, 14 Pin SOIC, TVSOP, and TSSOP (Top View)

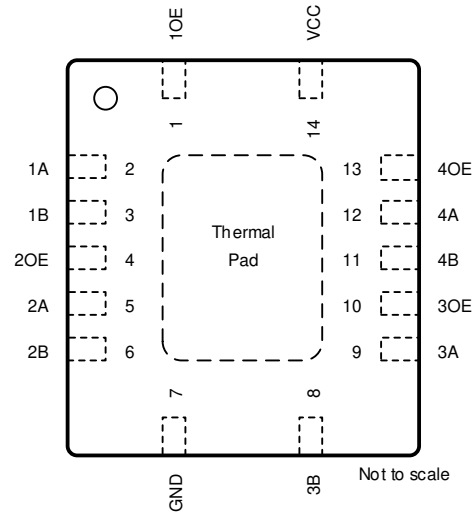


图 5-2. RGY Package, 14 Pin VQFN (Top View)

表 5-1. Pin Functions, D, DGV, PW, RGY

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1A	2	I/O	Channel 1 input or output
1B	3	I/O	Channel 1 input or output
10E	1	I	Output enable, active high
2A	5	I/O	Channel 2 input or output
2B	6	I/O	Channel 2 input or output
2OE	4	I	Output enable, active high
3A	9	I/O	Channel 3 input or output
3B	8	I/O	Channel 3 input or output
3OE	10	I	Output enable, active high
4A	12	I/O	Channel 4 input or output
4B	11	I/O	Channel 4 input or output
4OE	13	I	Output enable, active high
GND	7	—	Ground
V _{CC}	14	P	Power supply
Thermal Pad		—	Exposed thermal pad. There is no requirement to solder this pad; if connected, it should be left floating or tied to GND.

(1) I = input, O = output, I/O = input and output, P = power

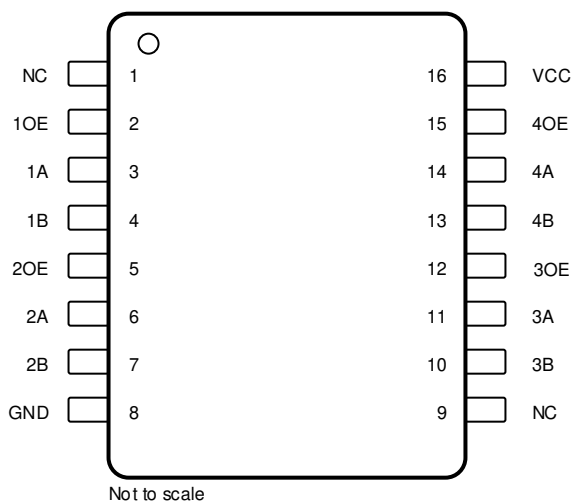


图 5-3. DBQ Package, 16 Pin SSOP (Top View)

表 5-2. Pin Functions, DBQ

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
1A	3	I/O	Channel 1 input or output
1B	4	I/O	Channel 1 input or output
1OE	2	I	Output enable, active high
2A	6	I/O	Channel 2 input or output
2B	7	I/O	Channel 2 input or output
2OE	5	I	Output enable, active high
3A	11	I/O	Channel 3 input or output
3B	10	I/O	Channel 3 input or output
3OE	12	I	Output enable, active high
4A	14	I/O	Channel 4 input or output
4B	13	I/O	Channel 4 input or output
4OE	15	I	Output enable, active high
GND	8	—	Ground
NC	9	—	No internal connection
V _{CC}	16	P	Power supply

(1) I = input, O = output, I/O = input and output, P = power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage range		−0.5	4.6	V
V _I	Input voltage range ⁽²⁾		−0.5	4.6	V
I _{I/O}	Continuous channel current			128	mA
I _{IK}	Input clamp current	V _{I/O} < 0		−50	mA
T _{stg}	Storage temperature range		−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±250	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		2.3	3.6	V
V _{IH}	High-level control input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	V _{CC}	V
		V _{CC} = 2.7 V to 3.6 V	2	V _{CC}	
V _{IL}	Low-level control input voltage	V _{CC} = 2.3 V to 2.7 V	0.7		V
		V _{CC} = 2.7 V to 3.6 V	0.8		
T _A	Operating free-air temperature		−40	85	°C

- (1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74CBTLV3126					UNIT
		D (SOIC)	DGV (TVSOP)	PW (TSSOP)	RGY (VQFN)	DBQ (SSOP)	
		14 PINS	14 PINS	14 PINS	14 PINS	16 Pins	
R _{θJA}	Junction-to-ambient thermal resistance	100.6	154.8	123.3	59.6	118.7	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	55.5	64.5	53.0	71.3	66.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	56.8	88.4	66.3	35.6	62.2	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	17.0	11.1	9.3	4.2	20.9	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	56.4	87.4	65.7	35.7	61.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	16.1	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IK}	$V_{CC} = 3\text{ V}$,	$I_I = -18\text{ mA}$				-1.2	V
I_I	$V_{CC} = 3.6\text{ V}$,	$V_I = V_{CC}$ or GND				± 1	μA
I_{off}	$V_{CC} = 0$,	V_I or $V_O = 0$ to 3.6 V				10	μA
I_{CC}	$V_{CC} = 3.6\text{ V}$,	$I_O = 0$,	$V_I = V_{CC}$ or GND			10	μA
ΔI_{CC} ⁽²⁾ Control inputs	$V_{CC} = 3.6\text{ V}$,	One input at 3 V ,	Other inputs at V_{CC} or GND			300	μA
C_i Control inputs	$V_I = 3\text{ V}$ or 0				2.5		pF
$C_{io(OFF)}$	$V_O = 3\text{ V}$ or 0 ,	OE = GND			7		pF
r_{on} ⁽³⁾	$V_{CC} = 2.3\text{ V}$, TYP at $V_{CC} = 2.5\text{ V}$	$V_I = 0$	$I_I = 64\text{ mA}$		5	8	Ω
			$I_I = 24\text{ mA}$		5	8	
		$V_I = 1.7\text{ V}$,	$I_I = 15\text{ mA}$		27	40	
	$V_{CC} = 3\text{ V}$	$V_I = 0$	$I_I = 64\text{ mA}$		5	7	
			$I_I = 24\text{ mA}$		5	7	
		$V_I = 2.4\text{ V}$,	$I_I = 15\text{ mA}$		10	15	

(1) All typical values are at $V_{CC} = 3.3\text{ V}$ (unless otherwise noted), $T_A = 25^\circ\text{C}$.

(2) This is the increase in supply current for each input that is at the specified voltage level, rather than V_{CC} or GND.

(3) Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

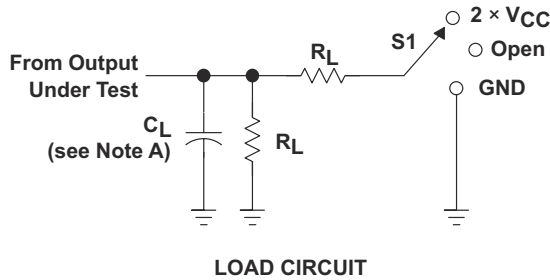
6.6 Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see [Figure 7-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 2.5\text{ V}$ $\pm 0.2\text{ V}$		$V_{CC} = 3.3\text{ V}$ $\pm 0.3\text{ V}$		UNIT
			MIN	MAX	MIN	MAX	
t_{pd} ⁽¹⁾	A or B	B or A		0.15		0.25	ns
t_{en}	OE	A or B	1.6	4.5	1.9	4.2	ns
t_{dis}	OE	A or B	1.3	4.7	1	4.8	ns

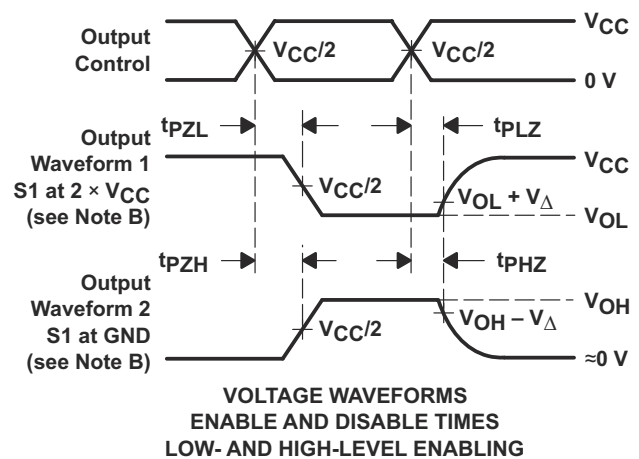
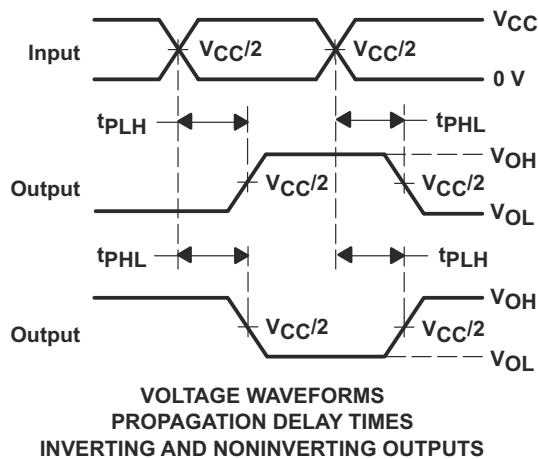
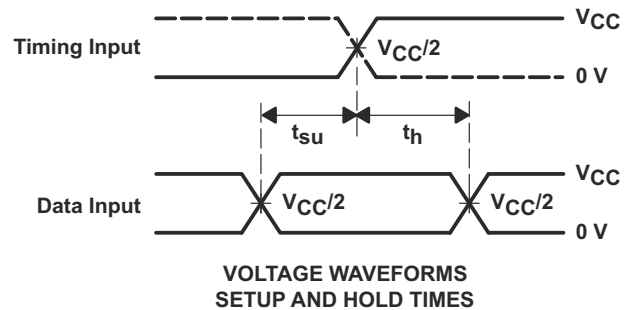
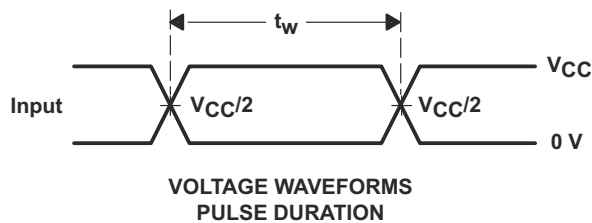
(1) The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

7 Parameter Measurement Information



TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	$2 \times V_{CC}$
t_{PHZ}/t_{PZH}	GND

V_{CC}	C_L	R_L	V_{Δ}
$2.5 \text{ V} \pm 0.2 \text{ V}$	30 pF	500 Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	50 pF	500 Ω	0.3 V



- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: $PPR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
- The outputs are measured one at a time with one transition per measurement.
- t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- t_{PZL} and t_{PZH} are the same as t_{en} .
- t_{PLH} and t_{PHL} are the same as t_{pd} .
- All parameters and waveforms are not applicable to all devices.

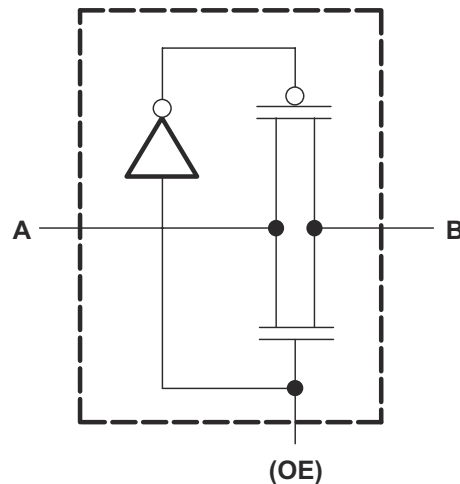
7-1. Load Circuit and Voltage Waveforms

8 Detailed Description

8.1 Overview

The SN74CBTLV3126 quadruple FET bus switch features independent line switches. Each switch is disabled when the associated output-enable (OE) input is low. This device is fully specified for partial-power-down applications using I_{off}. The I_{off} feature ensures that damaging current will not backflow through the device when it is powered down. The SN74CBTLV3126 device has isolation during power off. To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pull down resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

8.2 Functional Block Diagram



8.3 Feature Description

The SN74CBTLV3126 features 5-Ω switch connection between ports, allowing for low signal loss across the switch. Rail-to-rail switching on data I/O allows for full voltage swing outputs. I_{off} supports partial-power-down mode operation, protecting the chip from voltages at output ports when it is not powered on. Latch-up performance exceeds 100 mA per JESD 78, Class II.

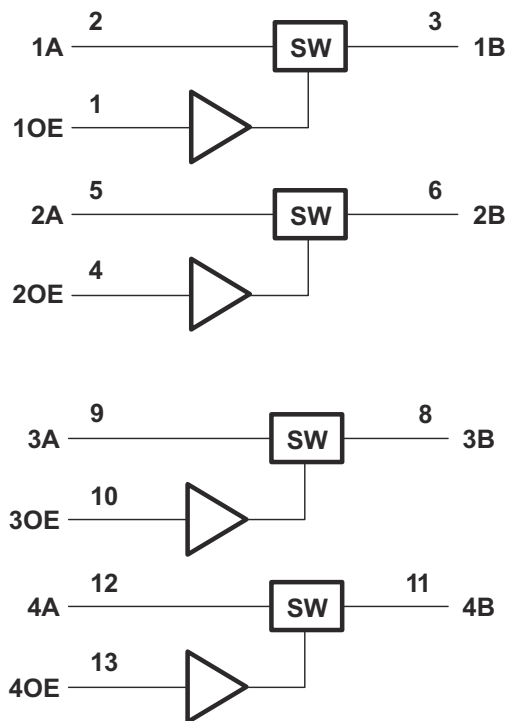
8.4 Device Functional Modes

8.4.1 Function Table (Each Bus Switch)

表 8-1 provides the truth table for the SN74CBTLV3126.

表 8-1. Truth Table

INPUT OE	FUNCTION
L	Disconnect
H	A port = B port



8-1. Logic Diagram (Positive Logic)

9 Application and Implementation

注

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

One useful application to take advantage of the SN74CBTLV3126 features is isolating various protocols from a processor or MCU such as JTAG, SPI, or standard GPIO signals. The device provides excellent isolation performance when the device is powered. The added benefit of powered-off protection allows a system to minimize complexity by eliminating the need for power sequencing in hot-swap and live insertion applications.

9.2 Typical Application

9.2.1 Protocol and Signal Isolation

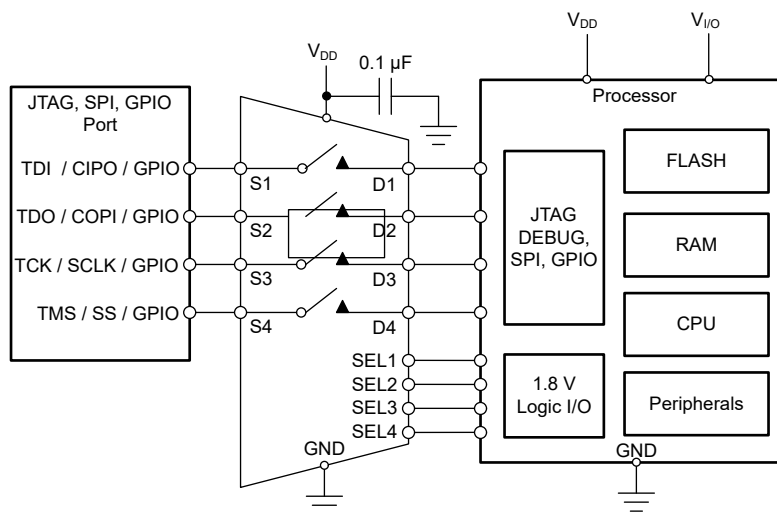


図 9-1. Typical Application

9.2.1.1 Design Requirements

For this design example, use the parameters listed in 表 9-1.

表 9-1. Design Parameters

PARAMETERS	VALUES
Supply (V _{DD})	3.3 V
Input or output signal range	0 V to 3.3 V
Control logic thresholds	1.8 V compatible

9.2.1.2 Detailed Design Procedure

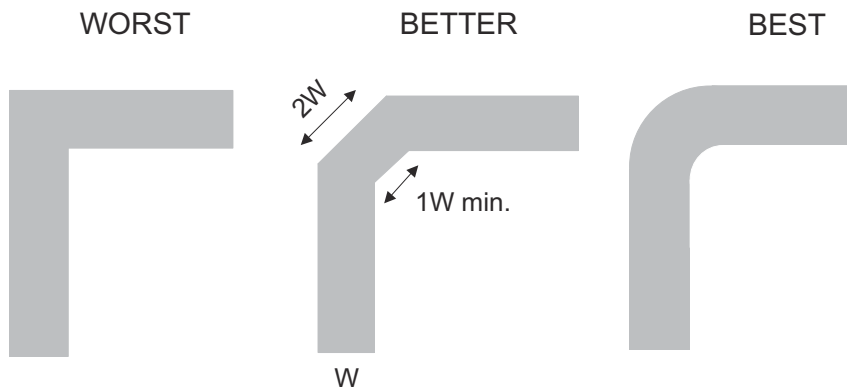
The SN74CBTLV3126 can operate without any external components except for the supply decoupling capacitors. TI recommends that the digital control pins (OE) be pulled up to V_{CC} or down to GND to avoid an undesired switch state that could result from the floating pin. All input signals passing through the switch must fall within the *Recommend Operating Conditions* of the SN74CBTLV3126 including signal range and continuous current. For this design example, with a supply of 3.3 V, the signals can range from 0 V to 3.3 V when the device is powered. This example can also utilize the Powered-off Protection feature, and the inputs can range from 0 V to 3.3 V when $V_{DD} = 0$ V.

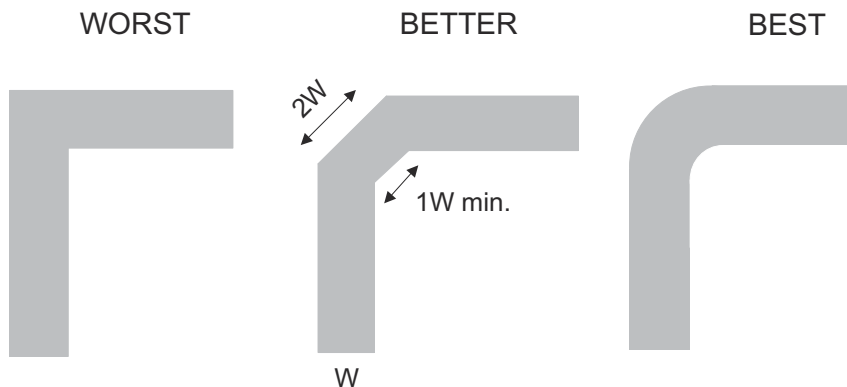
10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions* table. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, a 0.1- μ F bypass capacitor is recommended. If multiple pins are labeled V_{CC} , then a 0.01- μ F or 0.022- μ F capacitor is recommended for each V_{CC} because the V_{CC} pins are tied together internally. For devices with dual supply pins operating at different voltages, for example V_{CC} and V_{DD} , a 0.1- μ F bypass capacitor is recommended for each supply pin. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

11 Layout

11.1 Layout Guidelines

When a PCB trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self-inductance of the trace which results in the reflection. Not all PCB traces can be straight, and therefore; some traces must turn corners.  11-1 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.



 11-1. Trace Example

Route the high-speed signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points, through-hole pins are not recommended at high frequencies.

Do not route high speed signal traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or ICs that use or duplicate clock signals.

- Avoid stubs on the high-speed signals traces because they cause signal reflections.
- Route all high-speed signal traces over continuous GND planes, with no interruptions.
- Avoid crossing over anti-etch, commonly found with plane splits.

- When working with high frequencies, a printed circuit board with at least four layers is recommended; two signal layers separated by a ground and power layer as shown in [Figure 11-2](#).

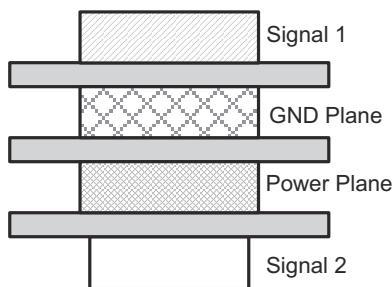


Figure 11-2. Example Layout

The majority of signal traces must run on a single layer, preferably Signal 1. Immediately next to this layer must be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies.

[Figure 11-3](#) shows an example of a PCB layout with the SN74CBTLV3126. Some key considerations are:

Decouple the V_{DD} pin with a 0.1- μ F capacitor, placed as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the V_{DD} supply.

High-speed switches require proper layout and design procedures for optimum performance.

Keep the input lines as short as possible.

Use a solid ground plane to help reduce electromagnetic interference (EMI) noise pickup.

Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

11.2 Layout Example

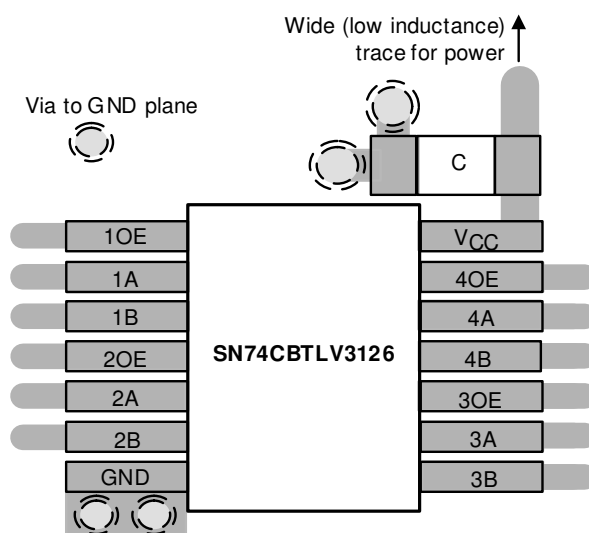


Figure 11-3. Example Layout

12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 サポート・リソース

[TI E2E™ サポート・フォーラム](#)は、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計に必要な支援を迅速に得ることができます。

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12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74CBTLV3126DBQRG4	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
74CBTLV3126DBQRG4.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
74CBTLV3126DBQRG4.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
74CBTLV3126DGVRG4	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
74CBTLV3126DGVRG4.B	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126D	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	-40 to 85	CBTLV3126
SN74CBTLV3126DBQR	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
SN74CBTLV3126DBQR.A	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
SN74CBTLV3126DBQR.B	Active	Production	SSOP (DBQ) 16	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
SN74CBTLV3126DGVR	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126DGVR.B	Active	Production	TVSOP (DGV) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126DR	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3126
SN74CBTLV3126DR.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3126
SN74CBTLV3126DR.B	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CBTLV3126
SN74CBTLV3126PW	Obsolete	Production	TSSOP (PW) 14	-	-	Call TI	Call TI	-40 to 85	CL126
SN74CBTLV3126PWR	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126PWR.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126PWR.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126PWRG4	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126PWRG4.A	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126PWRG4.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CL126
SN74CBTLV3126RGYR	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
SN74CBTLV3126RGYR.A	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126
SN74CBTLV3126RGYR.B	Active	Production	VQFN (RGY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	CL126

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74CBTLV3126DBQRG4	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
74CBTLV3126DGVRG4	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3126DBQR	SSOP	DBQ	16	2500	330.0	12.5	6.4	5.2	2.1	8.0	12.0	Q1
SN74CBTLV3126DGVR	TVSOP	DGV	14	2000	330.0	12.4	6.8	4.0	1.6	8.0	12.0	Q1
SN74CBTLV3126DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74CBTLV3126PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3126PWRG4	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74CBTLV3126RGYR	VQFN	RGY	14	3000	330.0	12.4	3.75	3.75	1.15	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74CBTLV3126DBQRG4	SSOP	DBQ	16	2500	353.0	353.0	32.0
74CBTLV3126DGVRG4	TVSOP	DGV	14	2000	353.0	353.0	32.0
SN74CBTLV3126DBQR	SSOP	DBQ	16	2500	353.0	353.0	32.0
SN74CBTLV3126DGVR	TVSOP	DGV	14	2000	353.0	353.0	32.0
SN74CBTLV3126DR	SOIC	D	14	2500	353.0	353.0	32.0
SN74CBTLV3126PWR	TSSOP	PW	14	2000	367.0	367.0	35.0
SN74CBTLV3126PWRG4	TSSOP	PW	14	2000	353.0	353.0	32.0
SN74CBTLV3126RGYR	VQFN	RGY	14	3000	353.0	353.0	32.0

D0014A**PACKAGE OUTLINE****SOIC - 1.75 mm max height**

SMALL OUTLINE INTEGRATED CIRCUIT



4220718/A 09/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

EXAMPLE BOARD LAYOUT

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

DGV (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

24 PINS SHOWN



- NOTES: A. All linear dimensions are in millimeters.
 B. This drawing is subject to change without notice.
 C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15 per side.
 D. Falls within JEDEC: 24/48 Pins – MO-153
 14/16/20/56 Pins – MO-194



DBQ0016A

PACKAGE OUTLINE

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



4214846/A 03/2014

NOTES:

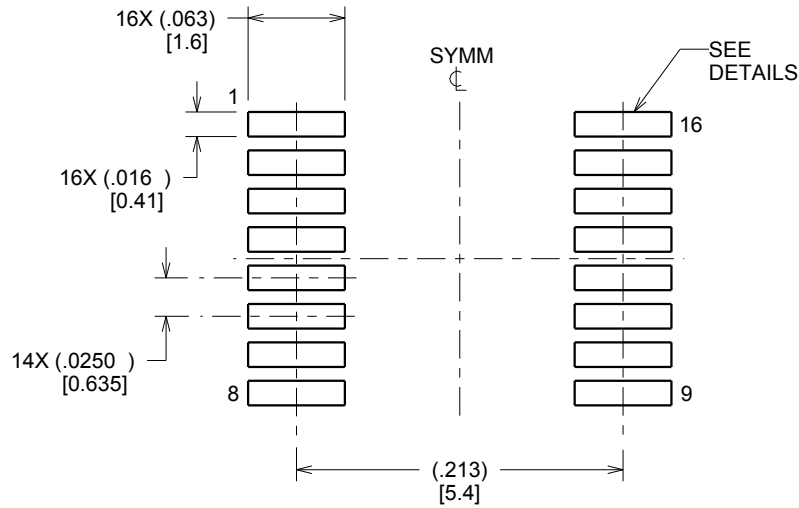
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 inch, per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MO-137, variation AB.

EXAMPLE BOARD LAYOUT

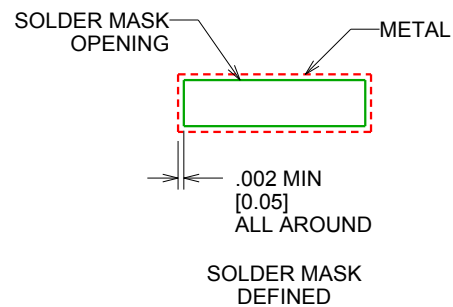
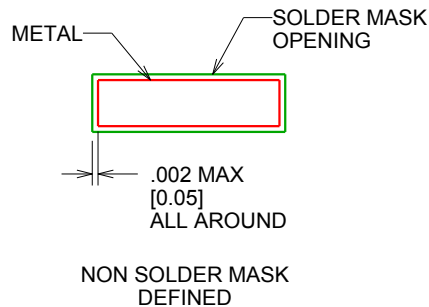
DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4214846/A 03/2014

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

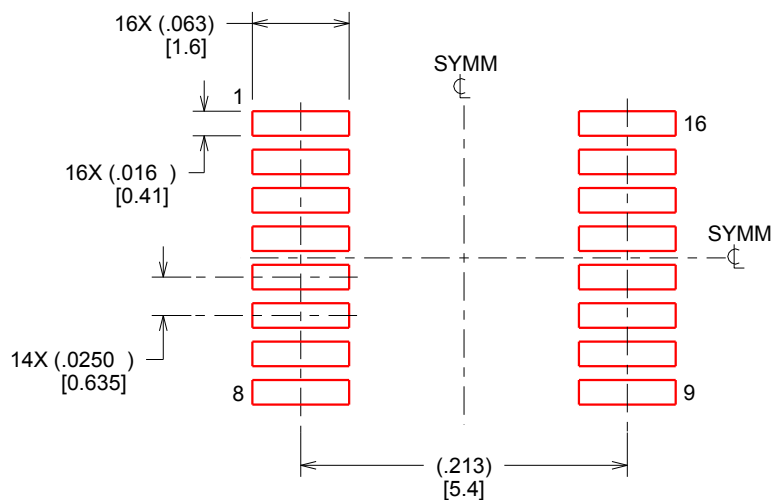
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBQ0016A

SSOP - 1.75 mm max height

SHRINK SMALL-OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.127 MM] THICK STENCIL
SCALE:8X

4214846/A 03/2014

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

RGY 14

VQFN - 1 mm max height

3.5 x 3.5, 0.5 mm pitch

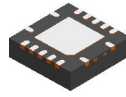
PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4231541/A

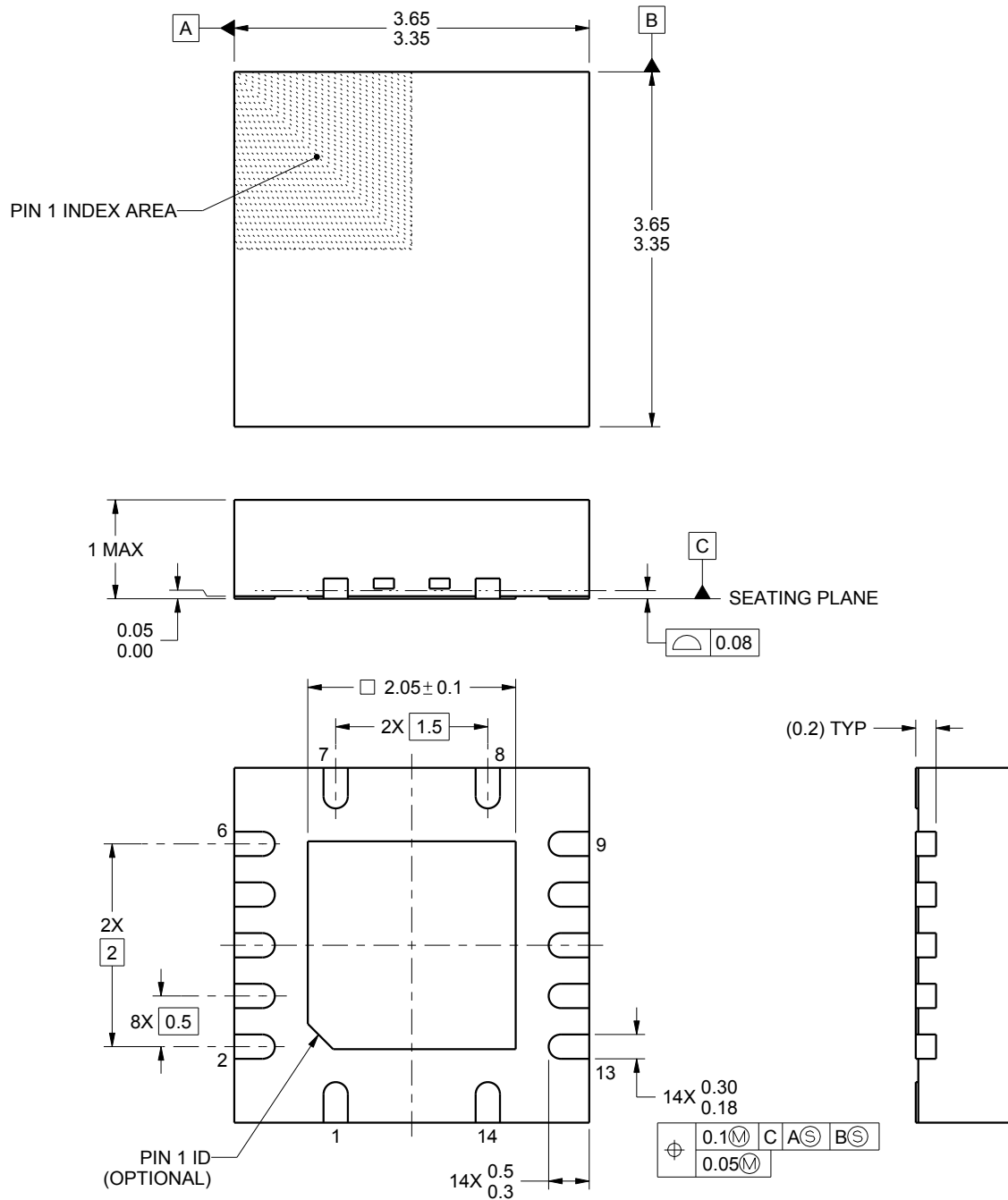
RGY0014A



PACKAGE OUTLINE

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



4219040/A 09/2015

NOTES:

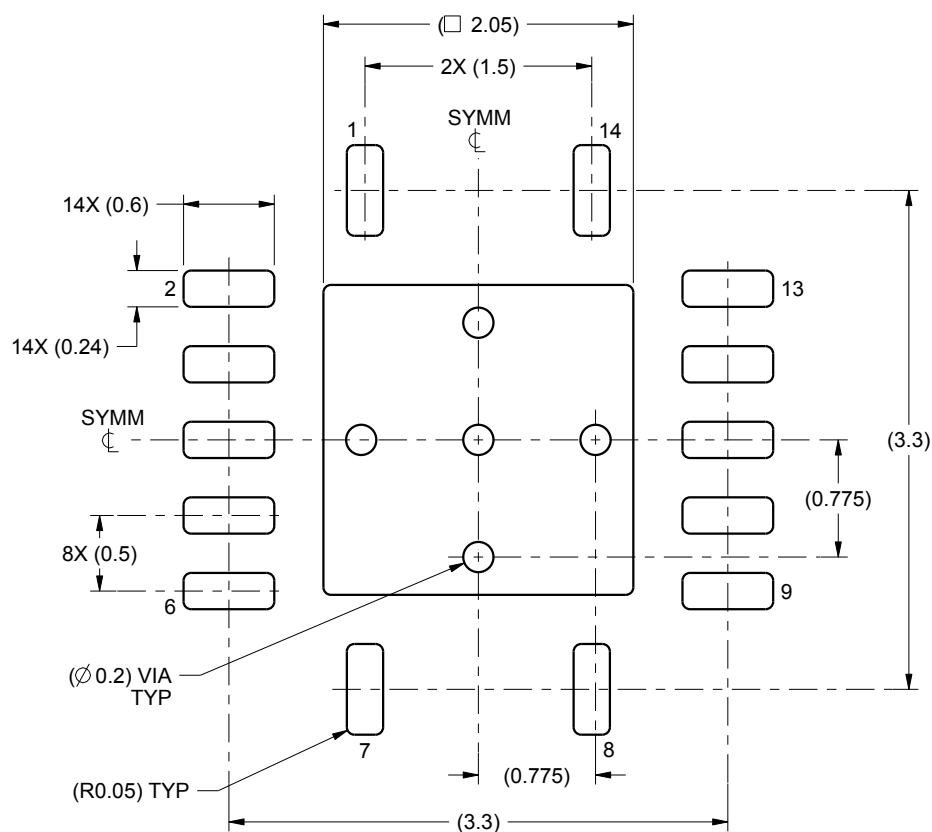
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

EXAMPLE BOARD LAYOUT

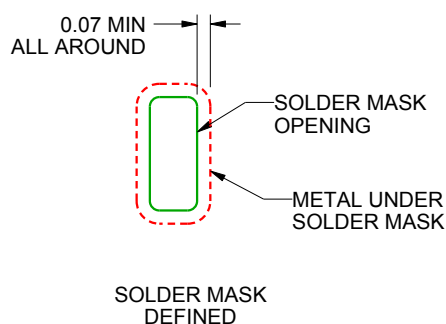
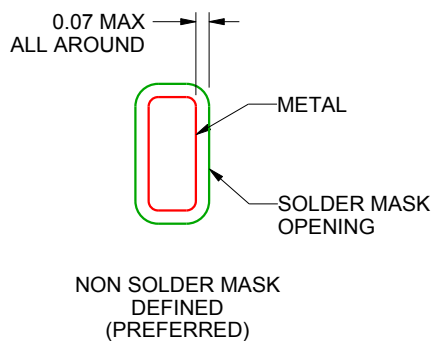
RGY0014A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



LAND PATTERN EXAMPLE
SCALE:20X



SOLDER MASK DETAILS

4219040/A 09/2015

NOTES: (continued)

- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slue271).

EXAMPLE STENCIL DESIGN

RGY0014A

VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:20X

4219040/A 09/2015

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PW0014A

PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220202/B 12/2023

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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郵送先住所：Texas Instruments, Post Office Box 655303, Dallas, Texas 75265
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